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AMENDMENT TO THE CLAIMS

Please amend the claims as follows:

Claims 1-16 (Canceled)

17. (Currently Amended) A process for treating a substrate comprising:  
forming a patterned ~~an~~ organic layer on said substrate; and  
reflowing said patterned organic layer at a substrate temperature from 15 degrees  
to 40 degrees centigrade while being exposed to an organic solvent-carrying gas.
18. (Currently Amended) The process as set forth in claim 17, wherein a deformed  
organic layer is formed from said patterned organic layer in said reflowing, and said  
deformed organic layer is thinner than said patterned organic layer.
19. (Currently Amended) The process as set forth in claim 18, wherein said deformed  
organic layer has a thickness that is equal to or less than one of one-fifth, one-tenth and  
one-half is equal in thickness to or less than a half of the thickness of said patterned  
organic layer.
20. (Currently Amended) The process as set forth in claim 17, wherein a chemical  
solution is penetrated into said patterned organic layer so as to dissolve part of said  
organic layer, thereby reflowing said patterned organic layer.

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21. (Currently Amended) The process as set forth in claim 17, wherein a chemical solution is penetrated into said patterned organic layer so as dissolve part of said patterned organic layer for the reflowing, and heat is applied to said patterned organic layer so as to reflow part of said patterned organic layer.

22. (Currently Amended) The process as set forth in claim 20, wherein said patterned organic layer is exposed to a gaseous mixture of organic solution comprising an organic solvent for making said chemical solution penetrate into said patterned organic layer.

23. (Currently Amended) The process as set forth in claim 21, wherein the process further comprises exposing said patterned organic layer is exposed to a high-temperature ambient at 50-300 degrees centigrade for applying the heat.

24. (Previously Presented) The process as set forth in claim 22, wherein a temperature of said gaseous mixture ranges from 15 degrees to 40 degrees centigrade.

25. (Currently Amended) The process as set forth in claim 20, wherein a deformed organic layer produced from said patterned organic layer is thinner than said patterned organic layer after the reflowing through the dissolution.

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26. (Previously Presented) The process as set forth in claim 20, wherein said chemical solution or said organic solution including said organic solvent comprises an organic solution comprising an organic solvent selected from the group consisting of alcohols expressed by a general formula of R-OH, alkoxyalcohols, ethers expressed by a general formula of R-O-R, Ar-O-R and Ar-O-Ar, esters, ketones, glycols, alkylene glycols, and glycol ethers where R is an alkyl group or a substituted alkyl group and Ar comprises a phenyl group or an aromatic ring other than said phenyl group.

27. (Currently Amended) The process as set forth in claim 17, wherein said patterned organic layer comprises a resist layer.

28. (Currently Amended) The process as set forth in claim 18, wherein a chemical solution is penetrated into said patterned organic layer so as to dissolve part of said organic layer, thereby reflowing said patterned organic layer.

29. (Currently Amended) The process as set forth in claim 19, wherein a chemical solution is penetrated into said patterned organic layer so as to dissolve part of said patterned organic layer, thereby reflowing said patterned organic layer.

30. (Currently Amended) The process as set forth in claim 18, wherein a chemical solution is penetrated into said patterned organic layer so as to dissolve part of said patterned organic layer for the reflowing, and heat is applied to said patterned organic layer so as to reflow part of said patterned organic layer.

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31. (Currently Amended) The process as set forth in claim 19, wherein a chemical solution is penetrated into said patterned organic layer so as to dissolve part of said patterned organic layer for the reflowing, and heat is applied to said patterned organic layer so as to reflow part of said patterned organic layer.

32. (Currently Amended) The process as set forth in claim 21, wherein said patterned organic layer is exposed to a gaseous mixture of organic solution comprising an organic solvent for making said chemical solution penetrate into said patterned organic layer.

33. (Currently Amended) The process as set forth in claim 21, wherein a deformed organic layer produced from said patterned organic layer is thinner than said patterned organic layer after the reflowing through the dissolution.

34. (Currently Amended) The process as set forth in claim 22, wherein a deformed organic layer produced from said patterned organic layer is thinner than said patterned organic layer after the reflowing through the dissolution.

35. (Currently Amended) The process as set forth in claim 23, wherein a deformed organic layer produced from said patterned organic layer is thinner than said patterned organic layer after the reflowing through the dissolution.

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36. (Currently Amended) The process as set forth in claim 24, wherein a deformed organic layer produced from said patterned organic layer is thinner than said patterned organic layer after the reflowing through the dissolution.

37. (Previously Presented) The process as set forth in claim 21, wherein said chemical solution or said organic solution including said organic solvent comprises an organic solution comprising an organic solvent selected from the group consisting of alcohols expressed by a general formula of R-OH, alkoxyalcohols, ethers expressed by a general formula of R-O-R, Ar-O-R and Ar-O-Ar, esters, ketones, glycols, alkylene glycols, and glycol ethers where R is an alkyl group or a substituted alkyl group and Ar comprises a phenyl group or an aromatic ring other than said phenyl group.

38. (Previously Presented) The process as set forth in claim 22, wherein said chemical solution or said organic solution including said organic solvent comprises an organic solution comprising an organic solvent selected from the group consisting of alcohols expressed by a general formula of R-OH, alkoxyalcohols, ethers expressed by a general formula of R-O-R, Ar-O-R and Ar-O-Ar, esters, ketones, glycols, alkylene glycols, and glycol ethers where R is an alkyl group or a substituted alkyl group and Ar comprises a phenyl group or an aromatic ring other than said phenyl group.

39. (Currently Amended) The process as set forth in claim 18, wherein said patterned organic layer comprises a resist layer.

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40. (Currently Amended) The process as set forth in claim 19, wherein said patterned organic layer comprises a resist layer.

41. (Currently Amended) The process as set forth in claim 20, wherein said patterned organic layer comprises a resist layer.

42. (Currently Amended) The process as set forth in claim 21, wherein said patterned organic layer comprises a resist layer.

43. (Currently Amended) The process as set forth in claim 22, wherein said patterned organic layer comprises a resist layer.

44. (Currently Amended) The process as set forth in claim 23, wherein said patterned organic layer comprises a resist layer.

45. (Currently Amended) The process as set forth in claim 24, wherein said patterned organic layer comprises a resist layer.

46. (Currently Amended) The process as set forth in claim 25, wherein said patterned organic layer comprises a resist layer.

47. (Currently Amended) The process as set forth in claim 26, wherein said patterned organic layer comprises a resist layer.